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B/O Form PTO-1449	Atty. Docket Number CHAN3228/EM	Serial Number 10/699.839
U.S. Department of Commerce Patent and Trademark Office	Applicant Edward Y. CHANG et. al.	
Information Disclosure Statement by Applicant	Filing Date November 4, 2003	Group Unassigned

U.S. Patent Documents

Examiner Initial	Document Number	Date	Patentee/Applicant	Class	Subclass	Filing Date if Appropriate
MAH	5,959,308	09/28/1999	Shichijo et. al.			01/29/1993
MAH	5,879,962	03/09/1999	DePuydt et. al.			12/13/1995
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Foreign Patent Documents

Examiner Initial	Document Number	Publication Date	Country/Agency	Class	Subclass	Translation	
						Yes	No

Other Documents (Including Author, Title, Date, Pertinent Pages, Place of Publication, Etc.)

MAH	J. A. Carlin et. al., <i>Impact of GaAs buffer thickness on electronic quality of GaAs grown on graded Ge/GeSi/Si substrates</i> , April 2000, American Institute of Physics, Applied Physics Letters, Vol. 76, No. 14, pp. 1884-1886.
MAH	R. D. Bringans et. al., <i>Use of ZnSe as an interlayer for GaAs growth on Si</i> , July 1992, American Institute of Physics, Applied Physics Letters, Vol. 61, No. 2, pp. 195-197.
MAH	J. Arokiaaraj et. al., <i>High-quality GaAs on Si substrate by the epitaxial lift-off technique using SeS₂</i> , December 1999, American Institute of Physics, Applied Physics Letters, Vol. 75, No. 24, pp. 3826-3828.
MAH	C. Kadow et. al., <i>Subpicosecond carrier dynamics in low-temperature grown GaAs on Si substrates</i> , October 1999, American Institute of Physics, Applied Physics Letters, Vol. 75, No. 17, pp. 2575-2577.
MAH	Y. R. Xing et. al., <i>Growth of high quality gallium arsenide on HF-etched silicon (001) by chemical beam epitaxy</i> , April 1993, American Institute of Physics, Applied Physics Letters, Vol. 62, No. 14, pp. 1653-1655.
MAH	Michael Y. Frankel et. al., <i>Integration of low-temperature GaAs on Si substrates</i> , January 1993, American Institute of Physics, Applied Physics Letters, Vol. 62, No. 3, pp. 255-257.

Examiner <i>Markuson</i>	Date Considered <i>06/14/05</i>
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EXAMINER: Initial if citation is considered, whether or not citation is in conformance with MPEP 609; Draw a line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



8/O Form PTO-1449 U.S. Department of Commerce Patent and Trademark Office Information Disclosure Statement by Applicant	Atty.CKET Number CHAN3228/REF	Serial Number 10/699.839
	Applicant Edward Y. CHANG et al.	
	Filing Date November 4, 2003	Group 2818

U.S. Patent Documents

Examiner Initial	Document Number	Date	Patentee/Applicant	Class	Subclass	Filing Date if Appropriate

Foreign Patent Documents

Examiner Initial	Document Number	Publication Date	Country/Agency	Class	Subclass	Translation	
						Yes	No
UK	092120501	28/07/2003	Taiwan (English Abstract)				
UK	092120502	28/07/2003	Taiwan (English Abstract)				

Other Documents (Including Author, Title, Date, Pertinent Pages, Place of Publication, Etc.)

Examiner <i>[Signature]</i>	Date Considered <i>06/14/05</i>
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